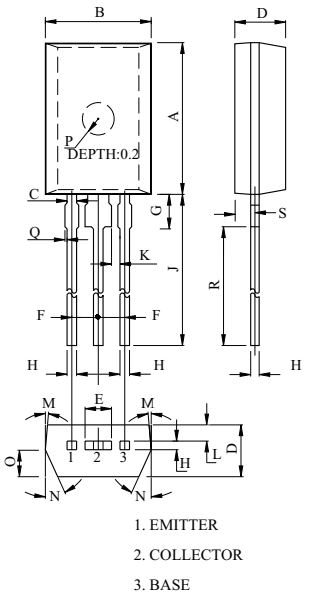
KTA1024

EPITAXIAL PLANAR PNP TRANSISTOR

HIGH VOLTAGE APPLICATION.

FEATURES

- High Voltage : V_{CEO}=-150V.
- Low Output Capacitance : C_{ob}=5.0pF(Max.).
- High Transition Frequency : f_T=120MHz (Typ.).
- Complementary to KTC3206.



DIM	MILLIMETERS
A	7.20 MAX
B	5.20 MAX
C	0.60 MAX
D	2.50 MAX
E	1.15 MAX
F	1.27
G	1.70 MAX
H	0.55 MAX
J	14.00±0.50
K	0.35 MIN
L	0.75±0.10
M	4°
N	25°
O	1.25
P	Φ1.50
Q	0.10 MAX
R	12.50±0.50
S	1.00

TO-92L

MAXIMUM RATING (Ta=25℃)

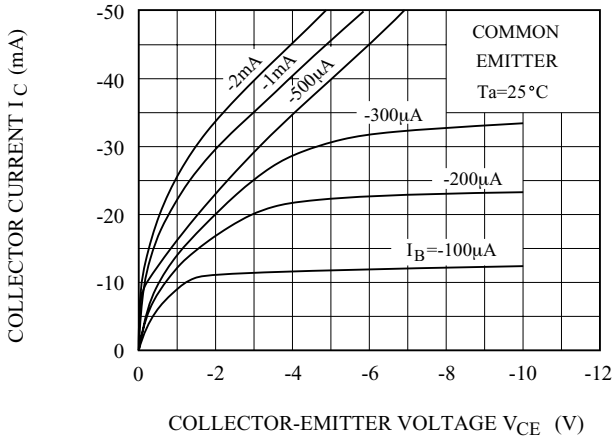
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-150	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-50	mA
Emitter Current	I_E	50	mA
Base Current	I_B	-5	mA
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25°...)

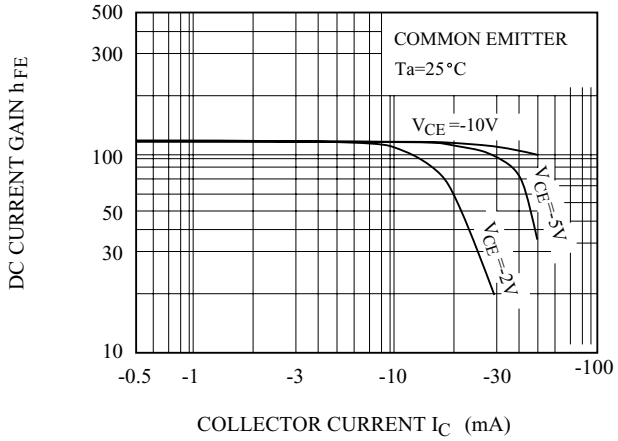
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-150V, I_E=0	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-0.1	μA
DC Current Gain	h_{FE}(Note)	V_{CE}=-5V, I_C=-10mA	70	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-10mA, I_B=-1mA	-	-	-0.8	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-5V, I_C=-30mA	-	-	-0.9	V
Transition Frequency	f_T	V_{CE}=-30V, I_C=-10mA	-	120	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	4.0	5.0	pF

Note : h_{FE} Classification O:70～140, Y:120～240

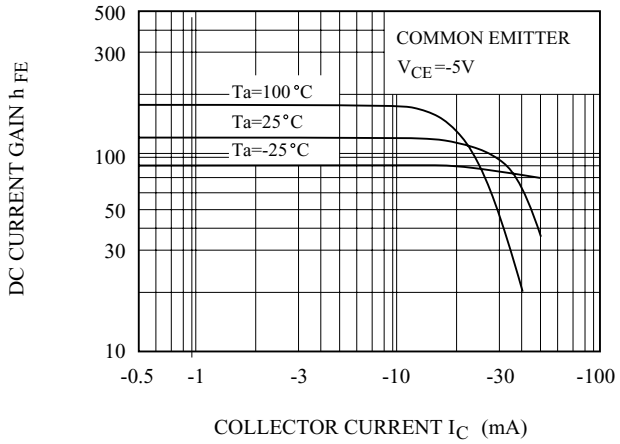
I_C - V_{CE}



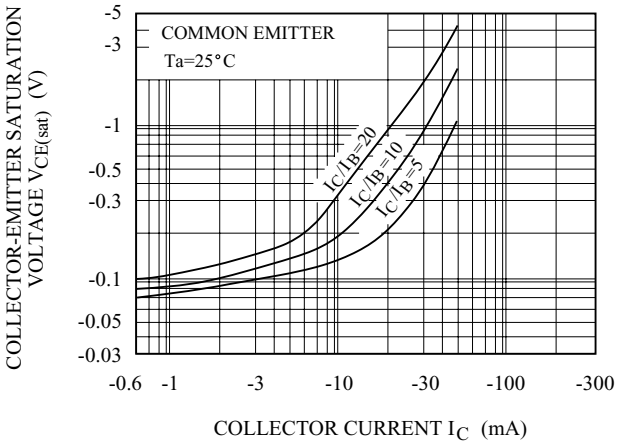
h_{FE} - I_C



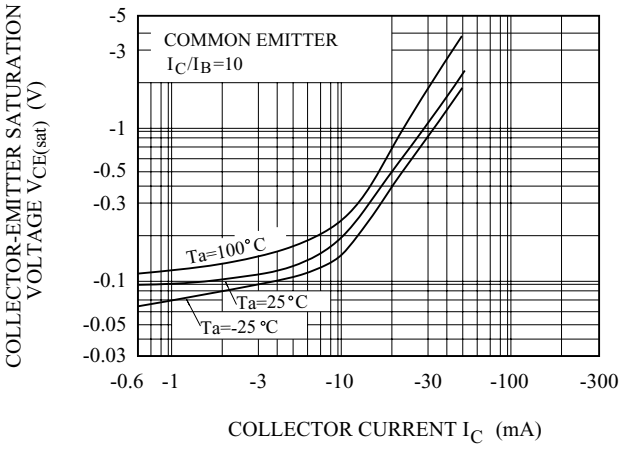
h_{FE} - I_C



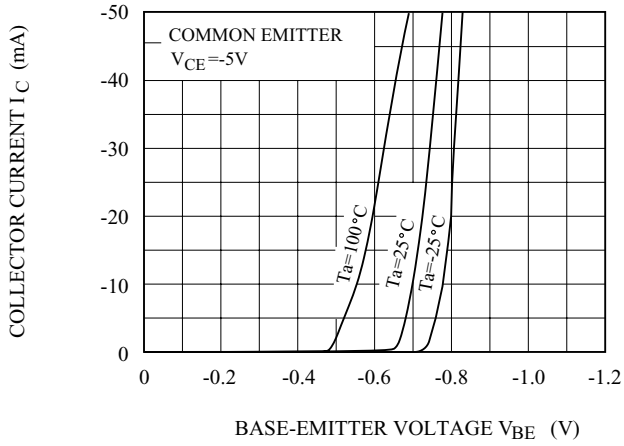
$V_{CE(sat)}$ - I_C



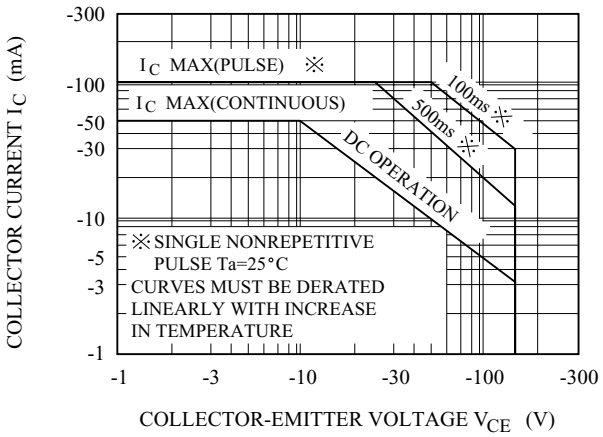
$V_{CE(sat)}$ - I_C



I_C - V_{BE}



SAFE OPERATING AREA



Pc - Ta

